Remarks:

We amended claims 1, 6, 9 and 10 under article 34 of PCT on November 28, 2005. Contents of Amendment are as follows:

(a) Re:claim 1

In claim 1, the phrase "at least one of a Si-containing material, a N-containing material and C-containing material" is changed to -at least one of a Si-containing material and a N-containing material—, and

the phrase "the metallic compound film contains the metal in the metal carbonyl and at least one of Si, N and C" is changed to -the metallic compound film contains the metal in the metal carbonyl and at least one of Si and N; and the work function of the metallic compound film can be controlled by changing the content of at least one of Si and N in the metallic compound film-.

The under-line part is amended part by this amendment.

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(b) Re:claim 6

Claim 6 is replaced with new one.

(c) Re:claim 9

Claim 9 is replaced with new one.

(d) Re:claim 10

In claim 10, the phrase "the gate electrode comprises: a metal-containing electrically conductive layer; a barrier layer formed on the electrically conductive layer; and a silicon film formed on the barrier layer" is changed to -the gate electrode comprises: a metallic compound film; a barrier layer formed on the metallic compound film; and a silicon film formed on the barrier layer-, and

the phrase "the barrier layer is formed by the use of a material containing a metal carbonyl, and at least one of a

N-containing material and a C-containing material; and the barrier layer is a film of a metallic compound containing the metal in the metal carbonyl and at least one of N and C" is changed to -the barrier layer is formed by the use of a material containing a metal carbonyl, a N-containing material, and a C-containing material; the barrier layer contains the metal in the metal carbonyl, N, and C; the metallic compound film is formed by the use of a material containing a metal carbonyl, and at least one of a Si-containing material and a N-containing material; the metallic compound film contains the metal in the metal carbonyl and at least one of Si and N; and the work function of the metallic compound film can be controlled by changing the content of at least one of Si and N in the metallic compound film-.

The under-line part is amended part by this amendment.